

Nch 600V 8A Power MOSFET

V _{DSS}	600V
R _{DS(on)} (Max.)	0.95Ω
I _D	8A
P_{D}	119W

● Features

- 1) Low on-resistance.
- 2) Fast switching speed.
- 3) Gate-source voltage (V_{GSS}) guaranteed to be $\pm 30V$.
- 4) Drive circuits can be simple.
- 5) Parallel use is easy.
- 6) Pb-free lead plating; RoHS compliant

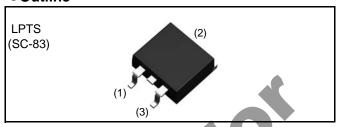
Application

Switching Power Supply

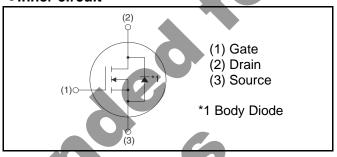
● Absolute maximum ratings(T_a = 25°C)

Parameter	Symbol	Value	Unit
Drain - Source voltage	$V_{ extsf{DSS}}$	600	V
Continuous drain current	I _D *1	±8	А
T _c = 100° C	I _D *1	±3.9	А
Pulsed drain current	I _{D,pulse} *2	±32	А
Gate - Source voltage	V_{GSS}	±30	V
Avalanche energy, single pulse	E _{AS} *3	4.3	mJ
Avalanche energy, repetitive	E _{AR} *4	3.4	mJ
Avalanche current	l _{AR} *3	4	А
Power dissipation $(T_c = 25^{\circ}C)$	P_{D}	119	W
Junction temperature	T _j	150	°C
Range of storage temperature	T _{stg}	-55 to +150	°C
Reverse diode dv/dt	dv/dt *5	15	V/ns

Outline



•Inner circuit



Packaging specifications

or ackaging specifications							
	Packaging	Taping					
	Reel size (mm)	330					
Type	Tape width (mm)	24					
Туре	Basic ordering unit (pcs)	1,000					
~ (2	Taping code	TL					
	Marking	R6008FNJ					

●Absolute maximum ratings

Parameter	Symbol	Conditions	Values	Unit
Drain - Source voltage slope	dv/dt	$V_{DS} = 480V, I_{D} = 8A$ $T_{j} = 125^{\circ}C$	50	V/ns

●Thermal resistance

Parameter	Symbol	Values			Unit
- Farameter	Symbol	Min.	Тур.	Max.	Offic
Thermal resistance, junction - case	R_{thJC}	-		1.05	°C/W
Thermal resistance, junction - ambient	R_{thJA}	-7/)'	80	°C/W
Soldering temperature, wavesoldering for 10s	T _{sold}		-	265	°C

•Electrical characteristics($T_a = 25$ °C)

Parameter	Symbol Conditions		Values			Unit
r arameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Drain - Source breakdown voltage	V _{(BR)DSS}	$V_{GS} = 0V$, $I_D = 1mA$	600	-	-	V
Drain - Source avalanche breakdown voltage	V _{(BR)DS}	$V_{GS} = 0V, I_{D} = 8A$	-	700	1	٧
		$V_{DS} = 600V, V_{GS} = 0V$				^
Zero gate voltage drain current	I _{DSS}	$T_j = 25^{\circ}C$	-	1	100	μΑ
		T _j = 125°C	ı	ı	10	mA
Gate - Source leakage current	I _{GSS}	$V_{GS} = \pm 30V, V_{DS} = 0V$	ı	ı	±100	nA
Gate threshold voltage	V _{GS (th)}	$V_{DS} = 10V$, $I_D = 1mA$	2.0	-	4.0	V
		$V_{GS} = 10V, I_D = 4A$				
Static drain - source on - state resistance	R _{DS(on)} *6	T _j = 25°C	-	0.73	0.95	Ω
		T _j = 125°C	-	1.62	-	
Gate input resistance	R_{G}	f = 1MHz, open drain	-	8.0	-	Ω

●Electrical characteristics(T_a = 25°C)

Parameter	Symbol	Conditions		Values		Unit
r ai ai i letei	Symbol	Conditions	Min.	Тур.	Max.	Offic
Transconductance	g _{fs} *6	$V_{DS} = 10V, I_D = 4.0A,$	2.5	5.0	1	S
Input capacitance	C _{iss}	$V_{GS} = 0V$	-	580	-	
Output capacitance	C _{oss}	V _{DS} = 25V	-	450		pF
Reverse transfer capacitance	C _{rss}	f = 1MHz	-	25		
Effective output capacitance, energy related	C _{o(er)}	$V_{GS} = 0V$	-	31.5	-	
Effective output capacitance, time related	C _{o(tr)}	$V_{DS} = 0V \text{ to } 480V$	C	31.8	-	pF
Turn - on delay time	t _{d(on)} *6	$V_{DD} \simeq 300V$, $V_{GS} = 10V$	<u> </u>	20	-	
Rise time	t _r *6	I _D = 4A	-	25	-	20
Turn - off delay time	t _{d(off)} *6	$R_L = 75\Omega$		60	120	ns
Fall time	t _f *6	$R_G = 10\Omega$		30	60	

●Gate Charge characteristics(T_a = 25°C)

Parameter	Symbol Conditions -		Values			Unit
raiailletei	Symbol	Conditions	Min.	Тур.	Max.	Offic
Total gate charge	Q_g^{*6}	V _{DD} ≃ 300V	-	20	ı	
Gate - Source charge	Q _{gs} *6	$I_D = 8A$	-	5	1	nC
Gate - Drain charge	Q _{gd} *6	V _{GS} = 10V	-	10	-	
Gate plateau voltage	V _(plateau)	$V_{DD} \simeq 300V, I_D = 8A$	-	5.7	-	V

^{*1} Limited only by maximum temperature allowed.

^{*2} Pw≤ 10μs, Duty cycle ≤ 1%

^{*3} L $^{\simeq}$ 500 μ H, V_{DD} = 50V, R_{G} = 25 Ω , starting T_{j} = 25°C

^{*4} L $^{\sim}$ 500 μ H, V_{DD} = 50V, R_G = 25 Ω , starting T_j = 25°C, f = 10kHz

^{*5} Reference measurement circuits Fig.5-1.

^{*6} Pulsed

ullet Body diode electrical characteristics (Source-Drain)(T_a = 25°C)

Parameter	Symbol	Symbol Conditions Values Min. Typ.			Unit	
Parameter	Symbol			Тур.	Max.	Offic
Inverse diode continuous, forward current	l _S *1	T _c = 25°C	-	,	8	A
Inverse diode direct current, pulsed	I _{SM} *2	I _c = 25°C	'	-	32	А
Forward voltage	V _{SD} *6	$V_{GS} = 0V$, $I_S = 8A$	-	-	1.5	V
Reverse recovery time	t _{rr} *6		-	67	ı	ns
Reverse recovery charge	Q _{rr} *6	I _S = 8A di/dt = 100A/us		0.17	ı	μС
Peak reverse recovery current	I _{rrm} *6	u., u. 10071 u.]	4.9	ı	А
Peak rate of fall of reverse recovery current	di _{rr} /dt	T _j = 25°C	-	610	-	A/μs

●Typical Transient Thermal Characteristics

Symbol	Value	Unit
R _{th1}	0.118	
R _{th2}	0.472	K/W
R _{th3}	0.583	

Symbol	Value	Unit
C _{th1}	0.0014	
C _{th2}	0.00402	Ws/K
C _{th3}	0.174	

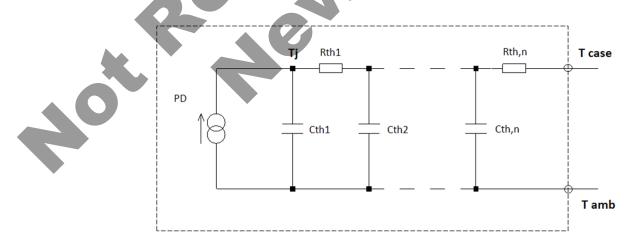


Fig.1 Power Dissipation Derating Curve

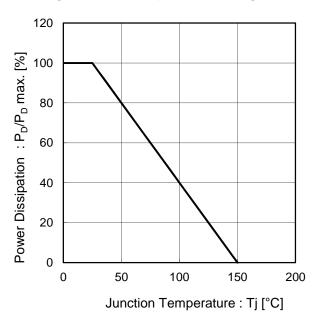
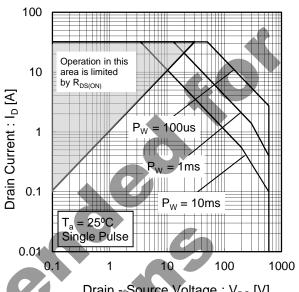
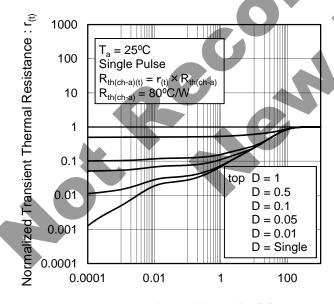


Fig.2 Maximum Safe Operating Area



Drain - Source Voltage : V_{DS} [V]

Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width



Pulse Width: P_W [s]

Fig.4 Avalanche Current vs Inductive Load

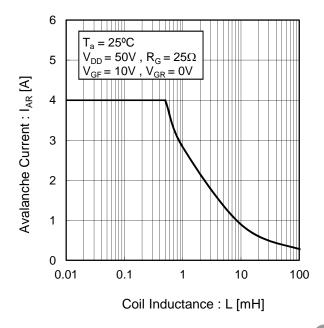


Fig.5 Avalanche Power Losses

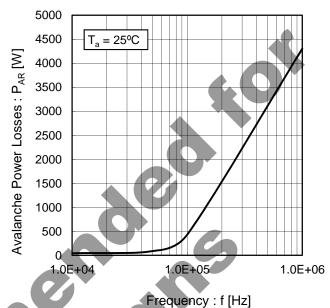
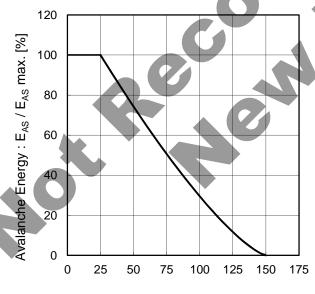
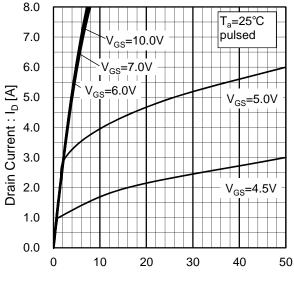


Fig.6 Avalanche Energy Derating Curve vs Junction Temperature



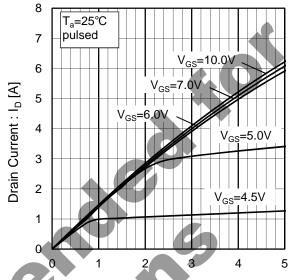
Junction Temperature : T_i [°C]

Fig.7 Typical Output Characteristics(I)



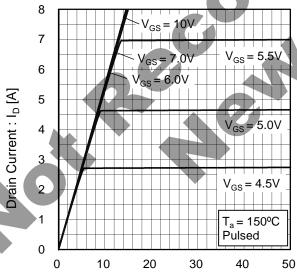
Drain - Source Voltage : V_{DS} [V]

Fig.8 Typical Output Characteristics(II)



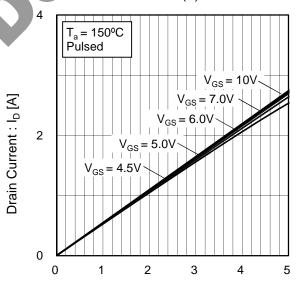
Drain - Source Voltage : V_{DS} [V]

Fig.9 T_j = 150°C Typical Output Characteristics(I)



Drain - Source Voltage : V_{DS} [V]

Fig.10 T_j = 150°C Typical Output Characteristics(II)



Drain - Source Voltage : V_{DS} [V]

Fig.11 Breakdown Voltage vs. Junction Temperature Drain - Source Breakdown Voltage : V_{(BR)DSS} [V] 900 850 800 750 700 650 600 550 500 -50 0 50 100 150 Junction Temperature : T_i [°C]

Fig.12 Typical Transfer Characteristics

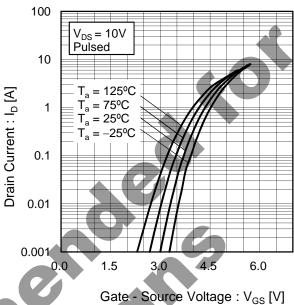


Fig.13 Gate Threshold Voltage vs. Junction Temperature

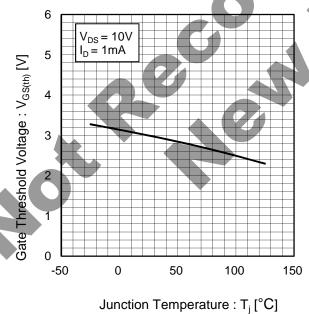
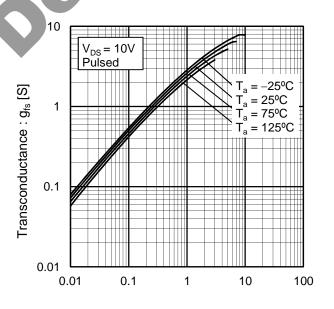


Fig.14 Transconductance vs. Drain Current





Drain Current : I_D [A]

Fig.15 Static Drain - Source On - State Resistance vs. Gate Source Voltage

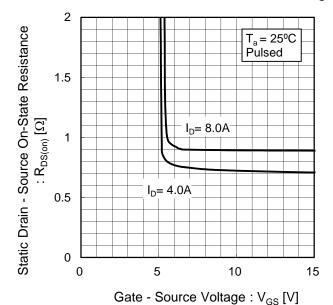


Fig.16 Static Drain - Source On - State Resistance vs. Junction Temperature

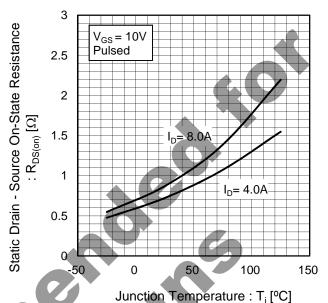


Fig.17 Static Drain - Source On - State Resistance vs. Drain Current

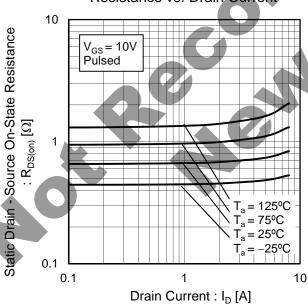
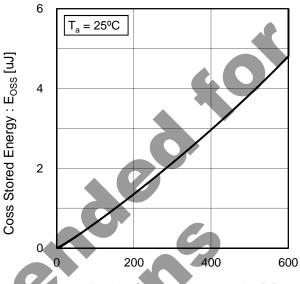


Fig.18 Typical Capacitance vs. Drain - Source Voltage 10000 C_{iss} 1000

Capacitance: C [pF] 100 10 f= 1MHz = 0V

0.1 100 1000 Drain - Source Voltage : V_{DS} [V]

Fig.19 Coss Stored Energy



Drain - Source Voltage : V_{DS} [V]

Fig.20 Switching Characteristics

0.01

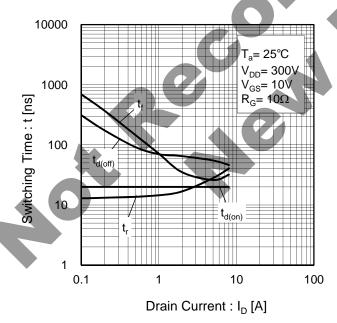


Fig.21 Dynamic Input Characteristics

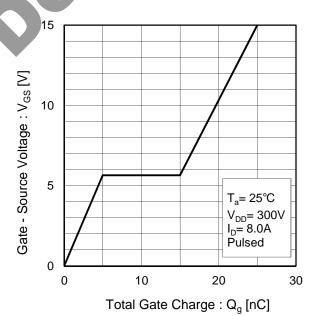
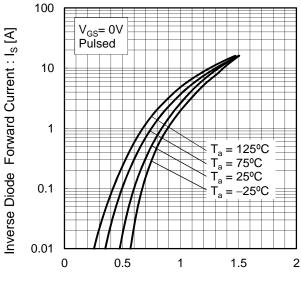
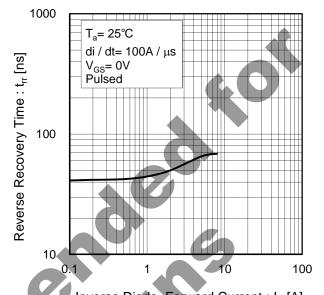


Fig.22 Inverse Diode Forward Current vs. Source - Drain Voltage



Source - Drain Voltage : V_{SD} [V]

Fig.23 Reverse Recovery Time vs.Inverse Diode Forward Current



Inverse Diode Forward Current: I_S [A]



Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

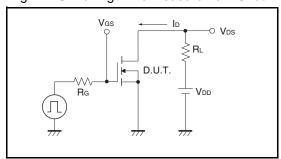


Fig.2-1 Gate Charge Measurement Circuit

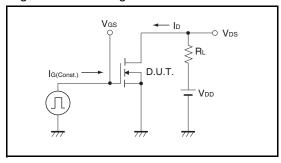


Fig.3-1 Avalanche Measurement Circuit

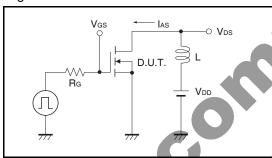


Fig.4-1 dv/dt Measurement Circuit

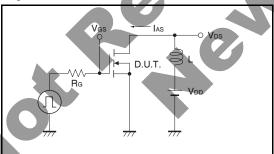


Fig.5-1 di/dt Measurement Circuit

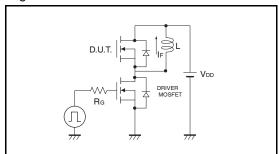


Fig.1-2 Switching Waveforms

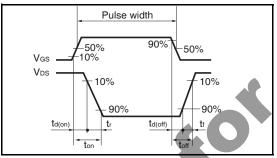


Fig.2-2 Gate Charge Waveform

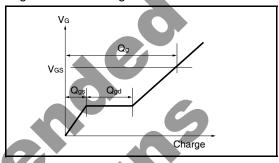


Fig.3-2 Avalanche Waveform

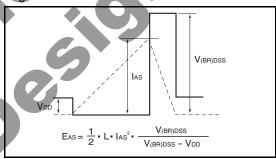


Fig.4-2 dv/dt Waveform

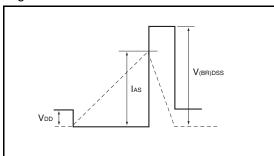
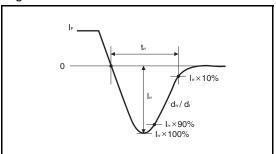
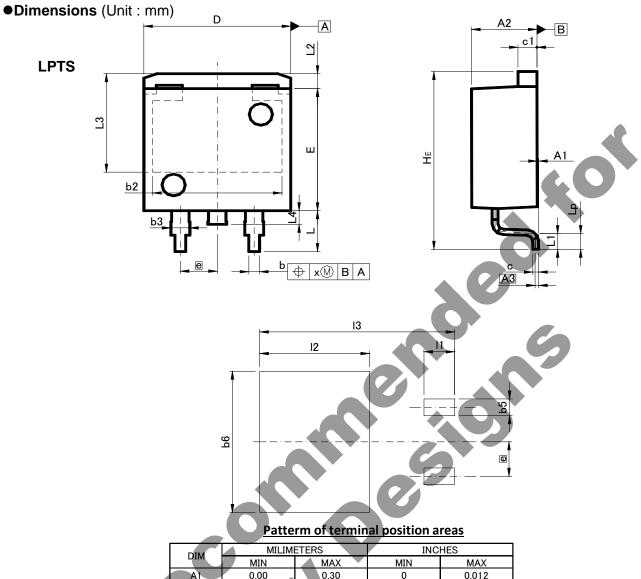


Fig.5-2 di/dt Waveform





			-	
DIM	MILIM	ETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
A1	0.00	0.30	0	0.012
A2	4.30	4.70	0.169	0.185
A3	0.3	25	0.0	01
b	0.68	0.98	0.027	0.039
▶ b2	8.	90	0.3	35
b3	1.14	1.44	0.045	0.057
С	0.30	0.60	0.012	0.024
c1	1.10	1.50	0.043	0.059
D	9.80	10.40	0.386	0.409
E	8.80	9.20	0.346	0.362
е	2.	54	0.10	
HE	12.80	13.40	0.504	0.528
L	2.70	3.30	0.106	0.13
L1	0.90	1.50	0.035	0.059
L2	1.	10	0.0	143
L3	7.:	25	0.2	85
L4	1.0	00	0.0	39
Lp	0.90	1.50	0.035	0.059
V		0.25		0.01

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b5	ı	1.23	ı	0.049
b6	İ	10.40	ı	0.409
11	ı	2.10	ı	0.083
12	_	7.55	_	0.297
13	_	13.40	_	0.528

Dimension in mm/inches

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JAPAN	USA	EU	CHINA
CLASSⅢ	CL ACCIII	CLASS II b	CLASSIII
CLASSIV	CLASSⅢ	CLASSⅢ	

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 - [e] Use of our Products in proximity to heat-producing components, plastic cords, or other flammable items
 - [f] Sealing or coating our Products with resin or other coating materials
 - [g] Use of our Products without cleaning residue of flux (even if you use no-clean type fluxes, cleaning residue of flux is recommended); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
 - [h] Use of the Products in places subject to dew condensation
- 4. The Products are not subject to radiation-proof design.
- 5. Please verify and confirm characteristics of the final or mounted products in using the Products.
- 6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse. is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power, exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
- 7. De-rate Power Dissipation depending on ambient temperature. When used in sealed area, confirm that it is the use in the range that does not exceed the maximum junction temperature.
- 8. Confirm that operation temperature is within the specified range described in the product specification.
- 9. ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

Precaution for Mounting / Circuit board design

- 1. When a highly active halogenous (chlorine, bromine, etc.) flux is used, the residue of flux may negatively affect product performance and reliability.
- 2. In principle, the reflow soldering method must be used on a surface-mount products, the flow soldering method must be used on a through hole mount products. If the flow soldering method is preferred on a surface-mount products, please consult with the ROHM representative in advance.

For details, please refer to ROHM Mounting specification

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- 1. If change is made to the constant of an external circuit, please allow a sufficient margin considering variations of the characteristics of the Products and external components, including transient characteristics, as well as static characteristics.
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This Product is electrostatic sensitive product, which may be damaged due to electrostatic discharge. Please take proper caution in your manufacturing process and storage so that voltage exceeding the Products maximum rating will not be applied to Products. Please take special care under dry condition (e.g. Grounding of human body / equipment / solder iron, isolation from charged objects, setting of lonizer, friction prevention and temperature / humidity control).

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- 1. Product performance and soldered connections may deteriorate if the Products are stored in the places where:
 - [a] the Products are exposed to sea winds or corrosive gases, including Cl2, H2S, NH3, SO2, and NO2
 - [b] the temperature or humidity exceeds those recommended by ROHM
 - [c] the Products are exposed to direct sunshine or condensation
 - [d] the Products are exposed to high Electrostatic
- 2. Even under ROHM recommended storage condition, solderability of products out of recommended storage time period may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is exceeding the recommended storage time period.
- 3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
- 4. Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

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